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Contents

v Conference Committee

	OPTO PLENARY SESSION
12001 02	Frontier electronics in memory of Professor Isamu Akasaki (Plenary Paper) [12001-501]
	FUNDAMENTAL PHYSICS AND CHARACTERIZATION
12001 03	Micro-photoluminescence to investigate lateral diffusion of charge carriers in InGaN/GaN MQWs [12001-16]
12001 04	Optimization of InGaN quantum well interfaces for fast interwell carrier transport and low nonradiative recombination [12001-17]
	DEGRADATION
12001 05	Deep defects in InGaN LEDs: modeling the impact on the electrical characteristics [12001-19]
12001 06	Micro-electroluminescence and micro-photoluminescence study on GaN-based laser diode aging [12001-20]
12001 07	GaN-based solar cells degradation kinetics investigated at high temperature under high-intensity 405nm optical stress [12001-21]
	VCSEL, SEMIPOLAR LASER DIODES, AND SINGLE-PHOTON EMITTERS
12001 08	Mode control in long cavity VCSELs with a curved mirror (Invited Paper) [12001-22]
	IN-PLANE LASER DIODES I
12001 09	Edge-emitting blue laser diode with high CW wall-plug efficiency of 50 $\%$ (Invited Paper) $[12001\text{-}26]$

	IN-PLANE LASER DIODES II
12001 0A	Lateral-longitudinal near-field measurements of 10 micrometer broad-ridge blue laser diodes [12001-33]
	UV LED
12001 OB	UV LED reliability: degradation mechanisms and challenges (Invited Paper) [12001-43]
12001 0C	On the performance and reliability of state-of-the-art commercial UV-C LEDs for disinfection purposes [12001-83]
	ELECTRONIC AND NANOSTRUCTURED DEVICES
12001 0D	Role of carbon in dynamic effects and reliability of 0.15 μm AlGaN/GaN HEMTs for RF power amplifiers $[12001\text{-}56]$
	POSTER SESSION
12001 OE	Physical failure analysis of stressed and proton-irradiated RF AlGaN-GaN HEMTs with Ni-Pd-Au Schottky contacts [12001-62]
12001 OF	Interdigitated electrode geometry variation and external quantum efficiency of GaN/AlGaN-based metal-semiconductor-metal UV photodetectors [12001-70]
12001 0G	LEDs on a GaN-on-Si wafer stacked with a Si-based circuit board through via holes [12001-71]